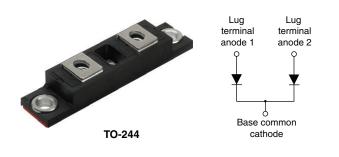
Vishay Semiconductors

High Performance Schottky Rectifier, 400 A



www.vishay.com

PRIMARY CHARACTERISTICS					
I _{F(AV)}	400 A				
V _R	45 V				
Package	TO-244				
Circuit configuration	Two diodes common cathode				

FEATURES

- 150 °C T_J operation
- Center tap module
- Very low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- UL approved file E222165
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

The VS-400CNQ045PbF center tap, high current, Schottky rectifier module has been optimized for very low forward voltage drop, with moderate leakage. The proprietary barrier technology allows for reliable operation up to 150 °C junction temperature. Typical applications are in switching power supplies, converters, freewheeling diodes, welding, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	CHARACTERISTICS VALUES UNIT					
I _{F(AV)}	Rectangular waveform	400	А			
V _{RRM}		45	V			
I _{FSM}	t _p = 5 μs sine	29 000	А			
V _F	200 A _{pk} , T _J = 125 °C (per leg)	0.52	V			
TJ	Range	-55 to +150	°C			

VOLTAGE RATINGS			
PARAMETER	SYMBOL	VS-400CNQ045PbF	UNITS
Maximum DC reverse voltage	V _R	45	V
Maximum working peak reverse voltage	V _{RWM}	45	v

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum average forward currentper leg	I=/			200		
See fig. 5 per device	I _{F(AV)}	50 % duty cycle at $T_C = 114$ °C, rectangular waveform				
Maximum peak one cycle non-repetitive surge current per leg		5 µs sine or 3 µs rect. pulse	Following any rated load condition and with rated	29 000	A	
See fig. 7	IFSM	10 ms sine or 6 ms rect. pulse	V _{RRM} applied	3400		
Non-repetitive avalanche energy per leg	E _{AS}	$T_J = 25 \text{ °C}, I_{AS} = 19 \text{ A}, L = 1 \text{ mH}$		180	mJ	
Repetitive avalanche current per leg		Current decaying linearly to ze Frequency limited by T _J maxin		40	А	

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VS-400CNQ045PbF

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ELECT	RICAL	SPECI	FICATI	ONS

ELECTRICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
		200 A	T.I = 25 °C	0.57	
Maximum forward voltage drop per leg	V _{EM} ⁽¹⁾	400 A	1j=25 C	0.73	v
See fig. 1	VFM (*)	200 A	T 105 %C	0.52	v
		400 A	– T _J = 125 °C	0.7	1
Maximum reverse leakage current per leg	I _{RM} ⁽¹⁾	T _J = 25 °C	V - Poted V	20	mA
See fig. 2	IRM (17	T _J = 125 °C	V _R = Rated V _R	1.2	А
Threshold voltage	V _{F(TO)}	T _J = T _J maximum		0.32	V
Forward slope resistance	r _t			0.81	mΩ
Maximum junction capacitance per leg	CT	$V_R = 5 V_{DC}$ (test signal range 100 kHz to 1 MHz), 25 °C		10 300	pF
Typical series inductance per leg	L _S	From top of terminal hole to mounting plane		5.0	nH
Maximum voltage rate of change	dV/dt	Rated V _R		10 000	V/µs

Note

 $^{(1)}\,$ Pulse width < 300 $\mu s,$ duty cycle < 2 %

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}	-55	-	150	°C			
Thermal resistance, junction to case per leg	P	-	-	0.19				
Thermal resistance, junction to case per module	R _{thJC}	-	-	0.095	°C/W			
Thermal resistance, case to heatsink	R _{thCS}				0.10	-		
Maight		-	68	-	g			
Weight		-	2.4	-	oz.			
Mounting torque		35.4 (4)		53.1 (6)				
Mounting torque center hole		30 (3.4)		40 (4.6)	lbf · in (N · m)			
Terminal torque		30 (3.4)	-	44.2 (5)	(
Vertical pull		-	-	80	llaf in			
2" lever pull		-	-	35	lbf · in			



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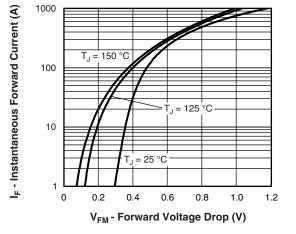


Fig. 1 - Maximum Forward Voltage Drop Characteristics (Per Leg)

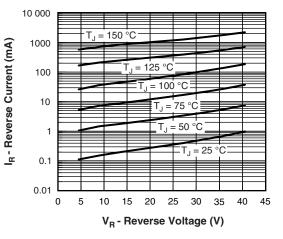


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage (Per Leg)

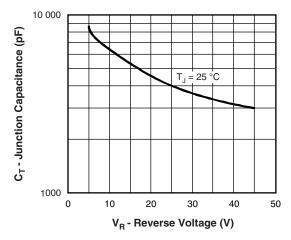


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

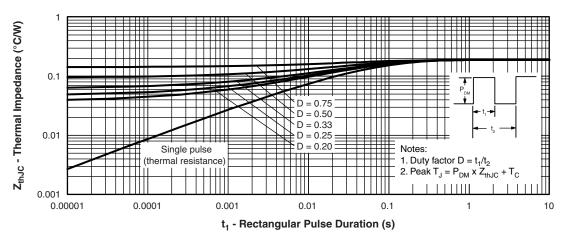


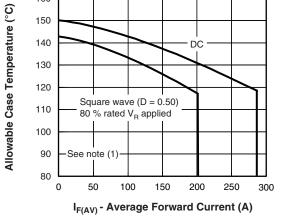
Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)

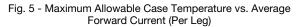
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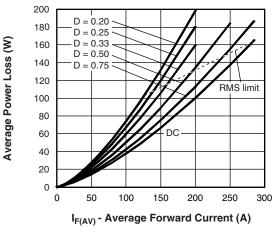
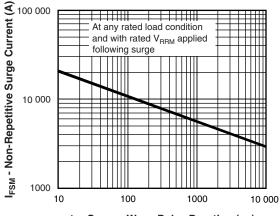


Fig. 6 - Forward Power Loss Characteristics (Per Leg)



 t_{p} - Square Wave Pulse Duration (µs)

Fig. 7 - Maximum Non-Repetitive Surge Current (Per Leg)

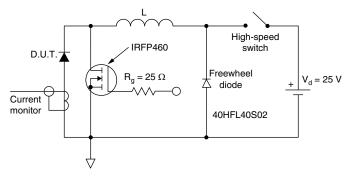


Fig. 8 - Unclamped Inductive Test Circuit

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \ \mathsf{x} \ \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ \mathsf{x} \ \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{80} \ \% \ \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

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ORDERING INFORMATION TABLE

Device code	vs-	40	0	с	Ν	Q	045	PbF
	1	2	3	4	5	6	7	8
	 Vishay Semiconductors product Average current rating (x 10) Product silicon identification C = circuit configuration 							
	5 - N = not isolated							
	6	- Q =	Schott	ky rectifi	er diode	;		
	7	· Vol	tage rati	ng (045	= 45 V))		
	8 -	- Lea	ıd (Pb)-f	ree				

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95021			



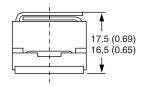


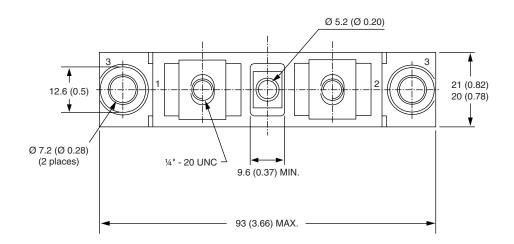
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TO-244

DIMENSIONS in millimeters (inches)









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